

X22C10 256 Bit 64 x 4

Nonvolatile Static RAM

FEATURES

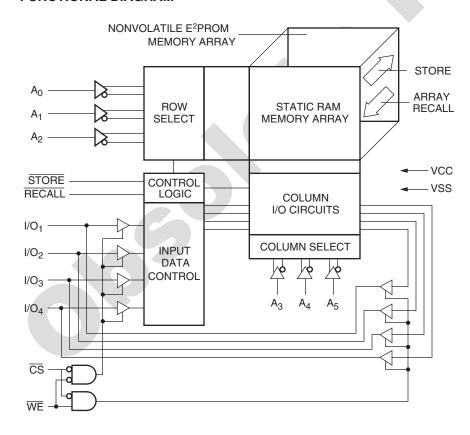
- High Performance CMOS —120ns RAM Access Time
- High Reliability
- -Store Cycles: 1,000,000 -Data Retention: 100 Years Low Power Consumption
- —Active: 40mA Max. —Standby: 100uA Max.
- Infinite Array Recall, RAM Read and Write Cycles
- Nonvolatile Store Inhibit: V_{CC} = 3.5V Typical
- Fully TTL and CMOS Compatible
- JEDEC Standard 18-Pin 300-mil DIP
- 100% Compatible with X2210 —With Timing Enhancements

DESCRIPTION

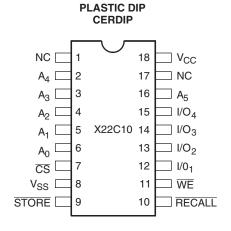
The X22C10 is a 64 x 4 CMOS NOVRAM featuring a high-speed static RAM overlaid bit-for-bit with a nonvolatile E²PROM. The NOVRAM design allows data to be easily transferred from RAM to E²PROM (STORE) and from E2PROM to RAM (RECALL). The STORE operation is completed within 5ms or less and the RECALL is completed within 1µs.

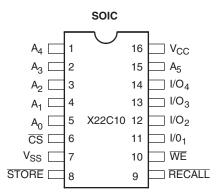
Xicor NOVRAMs are designed for unlimited write operations to the RAM, either RECALLs from E2PROM or writes from the host. The X22C10 will reliably endure 1,000,000 STORE cycles. Inherent data retention is greater than 100 years.

FUNCTIONAL DIAGRAM



PIN CONFIGURATION





PIN DESCRIPTIONS AND DEVICE OPERATION

Addresses (A₀-A₅)

The address inputs select a 4-bit memory location during a read or write operation.

Chip Select (CS)

The Chip Select input must be LOW to enable read or write operations with the RAM array. $\overline{\text{CS}}$ HIGH will place the I/O pins in the high impedance state.

Write Enable (WE)

The Write Enable input controls the I/O buffers, determining whether a RAM read or write operation is enabled. When $\overline{\text{CS}}$ is LOW and $\overline{\text{WE}}$ is HIGH, the I/O pins will output data from the selected RAM address locations. When both $\overline{\text{CS}}$ and $\overline{\text{WE}}$ are LOW, data presented at the I/O pins will be written to the selected address location.

Data In/Data Out (I/O₁-I/O₄)

Data is written to or read from the X22C10 through the I/O pins. The I/O pins are placed in the high impedance state when either $\overline{\text{CS}}$ is HIGH or during either a store or recall operation.

STORE

The $\overline{\text{STORE}}$ input, when LOW, will initiate the transfer of the entire contents of the RAM array to the E²PROM array. The $\overline{\text{WE}}$ and $\overline{\text{RECALL}}$ inputs are inhibited during the store cycle. The store operation is completed in 5ms or less.

A store operation has priority over RAM read/write operations. If STORE is asserted during a read operation, the read will be discontinued. If STORE is asserted during a RAM write operation, the write will be immediately terminated and the store performed. The data at the RAM address that was being written will be unknown in both the RAM and E²PROM arrays.

RECALL

The RECALL input, when LOW, will initiate the transfer of the entire contents of the E²PROM array to the RAM array. The transfer of data will be completed in 1µs or less.

An array recall has priority over RAM read/write operations and will terminate both operations when RECALL is asserted. RECALL LOW will also inhibit the STORE input.

Automatic Recall

Upon power-up the X22C10 will automatically recall data from the E²PROM array into the RAM array.

Write Protection

The X22C10 has three write protect features that are employed to protect the contents of the nonvolatile memory.

- V_{CC} Sense—All functions are inhibited when V_{CC} is <3.5V typical.
- Write Inhibit—Holding either STORE HIGH or RECALL LOW during power-up or power-down will prevent an inadvertent store operation and E²PROM data integrity will be maintained.
- Noise Protection—A STORE pulse of typically less than 20ns will not initiate a store cycle.

PIN NAMES

Symbol	Description
A ₀ -A ₅	Address Inputs
I/O ₁ -I/O ₄	Data Inputs/Outputs
WE	Write Enable
CS	Chip Select
RECALL	Recall
STORE	Store
V _{CC}	+5V
V _{SS}	Ground
NC	No Connect

ABSOLUTE MAXIMUM RATINGS

Temperature under Bias	65°C to +135°C
Storage Temperature	65°C to +150°C
Voltage on any Pin with	
Respect to V _{SS}	1V to +7V
D.C. Output Current	5mA
Lead Temperature	
(Soldering, 10 seconds)	300°C

COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and the functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Temperature	Min.	Max.
Commercial	0°C	+70°C
Industrial	−40°C	+85°C
Military	–55°C	+125°C

Supply Voltage	age Limits	
X22C10	5V ±10%	

D.C. OPERATING CHARACTERISTICS (Over the recommended operating conditions, unless otherwise specified.)

		Limits		Limits		Limits			
Symbol	Parameter	Min.	Max.	Units	Test Conditions				
Icc	V _{CC} Supply Current, RAM Read/Write		40	mA	$\overline{\text{CS}} = \text{V}_{\text{IL}}$, I/Os = Open, All Others = V_{IH} , Addresses = 0.4V/2.4V Levels @ f = 8MHz				
I _{SB1}	V _{CC} Standby Current (TTL Inputs)		2	mA	Store or Recall Functions Not Active, I/Os = Open, All Other Inputs = V _{IH}				
I _{SB2}	V _{CC} Standby Current (CMOS Inputs)		100	μΑ	Store or Recall functions Not Active, I/Os = Open, All Other Inputs = V_{CC} -0.3V				
ILI	Input Leakage Current		10	μA	V _{IN} = V _{SS} to V _{CC}				
I _{LO}	Output Leakage Current		10	μA	V _{OUT} = V _{SS} to V _{CC}				
V _{IL} ⁽²⁾	Input LOW Voltage		-1	0.8	V				
V _{IH} ⁽²⁾	Input HIGH Voltage		2	V _{CC} + 1	V				
V _{OL}	Output LOW Voltage		0.4	V	I _{OL} = 4.2mA				
V _{OH}	Output HIGH Voltage	2.4		V	I _{OH} = -2mA				

CAPACITANCE $T_A = +25$ °C, f = 1MHZ, $V_{CC} = 5$ V

Symbol	Parameter	Max.	Units	Test Conditions
C _{I/O} ⁽¹⁾	Input/Output Capacitance	8	pF	V _{I/O} = 0V
C _{IN} ⁽¹⁾	Input Capacitance	6	pF	V _{IN} = 0V

Notes: (1) This parameter is periodically sampled and not 100% tested.

(2) V_{IL} min. and V_{IH} max. are for reference only and are not tested.

MODE SELECTION

CE	WE	RECALL	STORE	I/O	Mode
Н	Х	Н	Н	Output High Z	Not Selected ⁽³⁾
L	Н	Н	Н	Output Data	Read RAM
L	L	Н	Н	Input Data HIGH	Write "1" RAM
L	L	Н	Н	Input Data LOW	Write "0" RAM
Х	Н	L	Н	Output High Z	Array Recall
Н	Х	L	Н	Output High Z	Array Recall
Х	Н	Н	L	Output High Z	Nonvolatile Store ⁽⁴⁾
Н	Х	Н	L	Output High Z	Nonvolatile Store ⁽⁴⁾

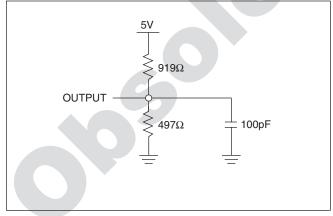
ENDURANCE AND DATA RETENTION

Parameter	Min.		Units
Endurance	100,000		Data Changes Per Bit
Store Cycles	1,000,000	<u> </u>	Store Cycles
Data Retention	100		Years

POWER-UP TIMING

Symbol	Parameter	Max.	Units
t _{PUR} (5)	Power-up to Read Operation	100	μs
t _{PUW} ⁽⁵⁾	Power-up to Write or Store Operation	5	ms

EQUIVALENT A.C. LOAD CIRCUIT



Notes: (3) Chip is deselected but may be automatically completing a store cycle.

- (4) STORE = LOW is required only to initiate the store cycle, after which the store cycle will be automatically completed (e.g. STORE = X).
- (5) t_{PUR} and t_{PUW} are the delays required from the time V_{CC} is stable until the specified operation can be initiated. These parameters are periodically sampled and not 100% tested.

A.C. CONDITIONS OF TEST

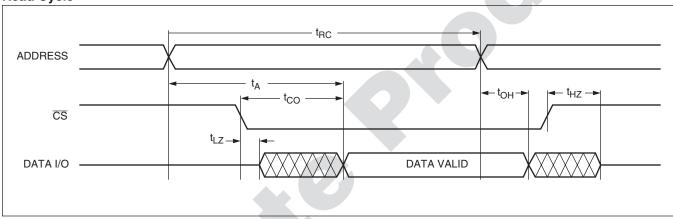
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	10ns
Input and Output Timing Levels	1.5V

A.C. CHARACTERISTICS (Over the recommended operating conditions, unless otherwise specified.

Read Cycle Limits

Symbol	Parameter	Min.	Max.	Units
t _{RC}	Read Cycle Time	120		ns
t _{AA}	Access Time		120	ns
t _{CO}	Chip Select to Output Valid		120	ns
t _{OH}	Output Hold from Address Change	0		ns
t _{LZ} ⁽⁶⁾	Chip Select to Output in Low Z	0		ns
t _{HZ} ⁽⁶⁾	Chip Deselect to Output in High Z		50	ns

Read Cycle

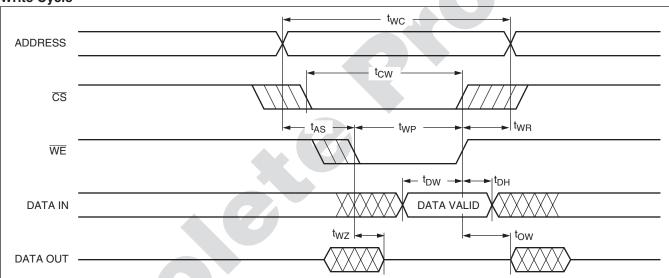


Note: (6) t_{LZ} min. and t_{HZ} min. are periodically sampled and not 100% tested.

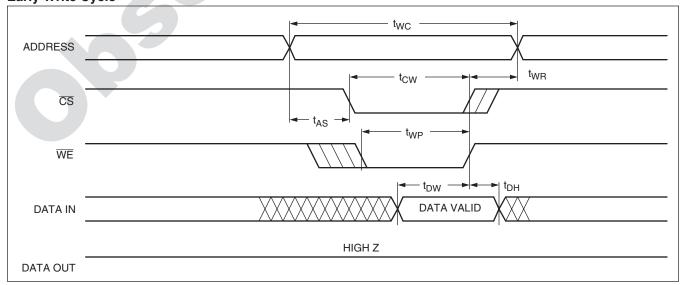
Write Cycle Limits

Symbol	Parameter	Min.	Max.	Units
t _{WC}	Write Cycle Time	120		ns
t _{CW}	Chip Select to End of Write	90		ns
t _{AS}	Address Setup Time	0		ns
t_{WP}	Write Pulse Width	90		ns
t _{WR}	Write Recovery Time	0		ns
t _{DW}	Data Valid to End of Write	40		ns
t _{DH}	Data Hold Time	0		ns
t _{WZ}	Write Enable to Output in High Z		50	ns
t _{OW}	Output Active from End of Write	0		ns

Write Cycle



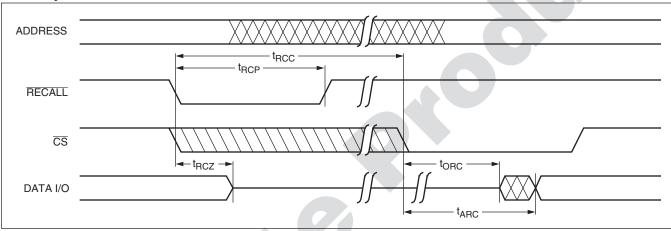
Early Write Cycle



Recall Cycle Limits

Symbol	Parameter	Min.	Max.	Units
t _{RCC}	Array Recall Time		1	μs
t _{RCP} ⁽⁷⁾	Recall Pulse Width	90		ns
t _{RCZ}	Recall to Output in High Z		50	ns
t _{ORC}	Output Active from End of Recall	0		ns
t _{ARC}	Recalled Data Access Time from End of Recall		150	ns

Recall Cycle

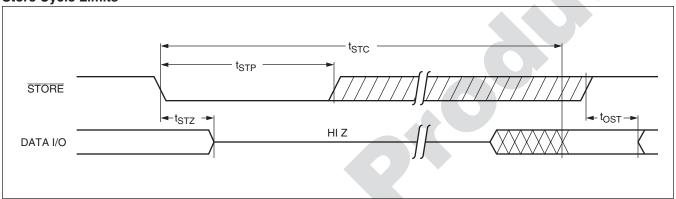


Notes: (7) $\overline{\text{Recall}}$ rise time must be less than 1 μ s.

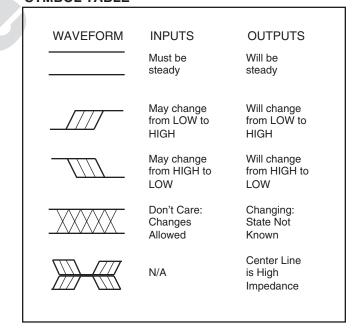
Store Cycle Limits

Symbol	Parameter	Min.	Max.	Units
t _{STC}	Internal Store Time		5	ms
t _{STP}	Store Pulse Width	90		ns
t _{STZ}	Store to Output in High Z		50	ns
t _{OST}	Output Active from End of Store	0		ns

Store Cycle Limits

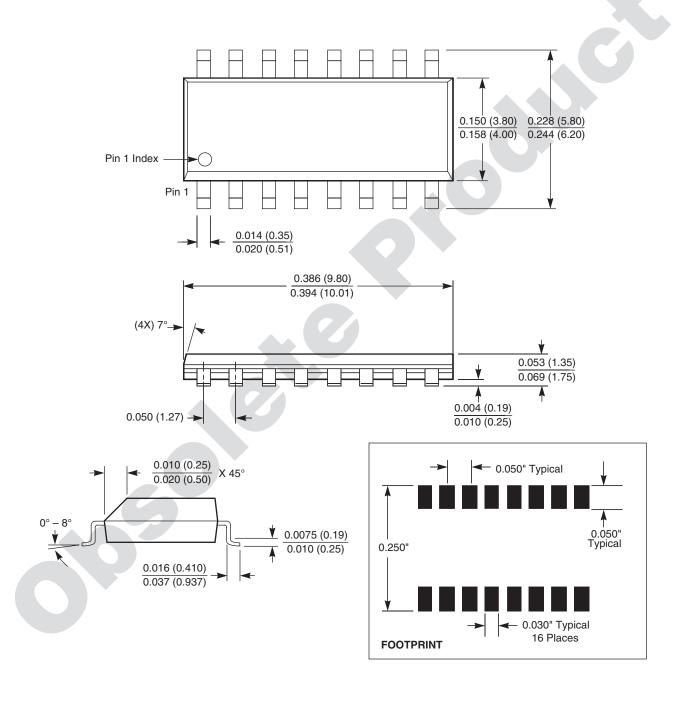






PACKAGING INFORMATION

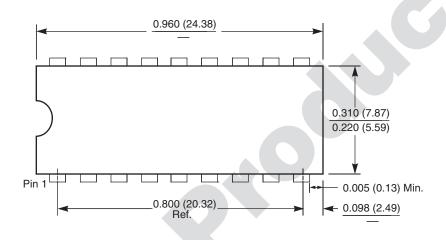
16-Lead Plastic Small Outline Gull Wing Package Type S

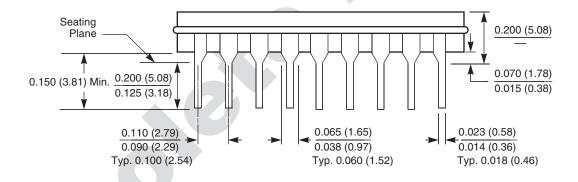


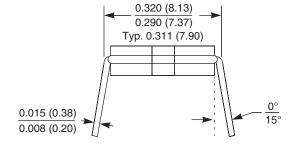
NOTE: ALL DIMENSIONS IN INCHES (IN PARENTHESES IN MILLIMETERS)

PACKAGING INFORMATION

18-Lead Hermetic Dual In-Line Package Type D





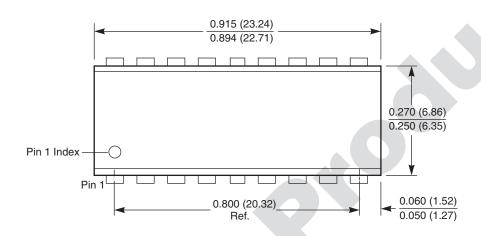


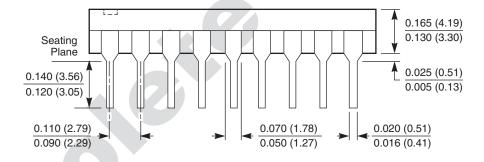
NOTE: ALL DIMENSIONS IN INCHES (IN PARENTHESES IN MILLIMETERS)

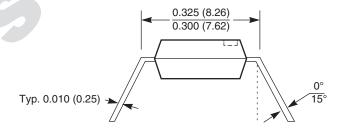
Characteristics subject to change without notice.

PACKAGING INFORMATION

18-Lead Plastic Dual In-line Package Type P



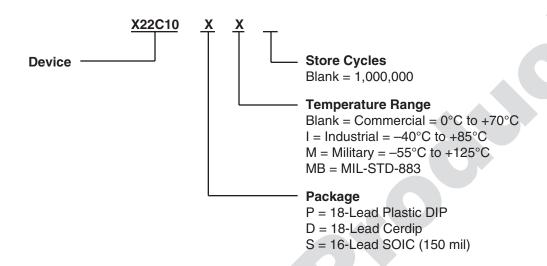




NOTE:

- 1. ALL DIMENSIONS IN INCHES (IN PARENTHESES IN MILLIMETERS)
- 2. PACKAGE DIMENSIONS EXCLUDE MOLDING FL ASH

ORDERING INFORMATION



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U.S. PATENTS

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LIFE RELATED POLICY

In situations where semiconductor component failure may endanger life, system designers using this product should design the system with appropriate error detection and correction, redundancy and back-up features to prevent such an occurrence.

Xicor's products are not authorized for use in critical components in life support devices or systems.

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.